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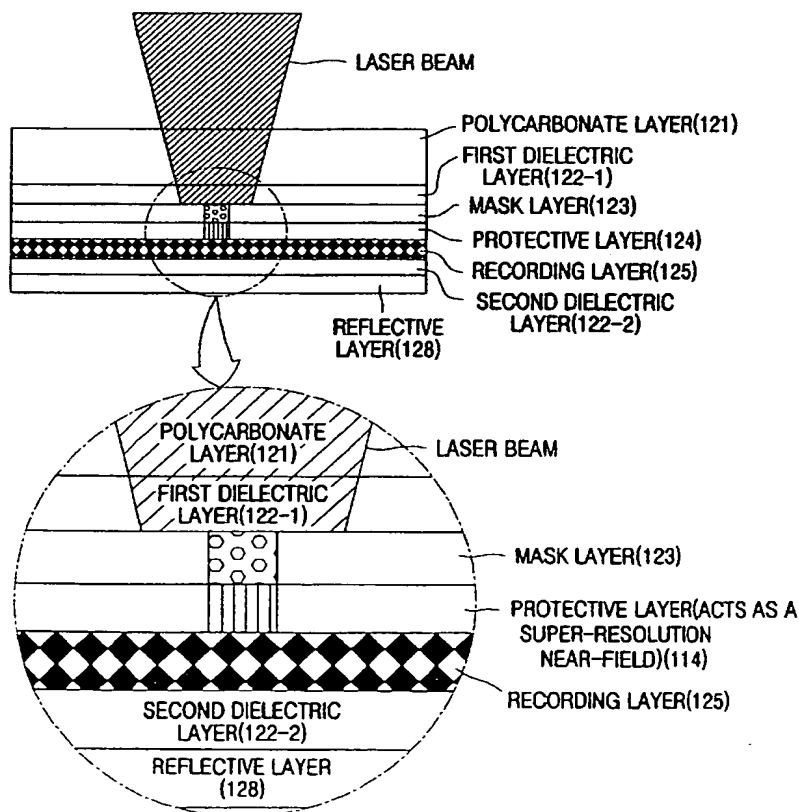
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[Continued on next page]

(54) Title: **HIGH DENSITY RECORDING MEDIUM WITH SUPER-RESOLUTION NEAR-FIELD STRUCTURE MANUFACTURED USING HIGH-MELTING POINT METAL OXIDE OR SILICON OXIDE MASK LAYER**



(57) Abstract: A high density recording medium with a super-resolution near-field structure including a mask layer comprising high melting point metal oxide or silicon oxide is provided. More particularly, A high density recording medium with a super-resolution near-field structure including a sequential stack of a second dielectric layer, a recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer, wherein the mask layer comprises high melting point metal oxide or silicon oxide to generate a near field by optically or thermally inducing physical changes in the crystalline structure and optical properties of the high melting point metal oxide or silicon oxide is provided.